

N-Channel Power MOSFET

600V, 0.6A, 5Ω

FEATURES

- Robust high voltage termination
- Avalanche energy specified
- Diode is characterized for use in bridge circuits
- Source to Drain diode recovery time comparable to a discrete fast recovery diode.

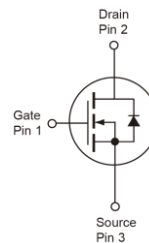
KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
V_{DS}	600	V
$R_{DS(on)}$ (max)	5	Ω
Q_g	13	nC

APPLICATION

- Power Supply
- Lighting
- Charger



SOT-223



Notes: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current ^(Note 1)	I_D	$T_C = 25^\circ\text{C}$	0.6
		$T_C = 100^\circ\text{C}$	0.36
Pulsed Drain Current ^(Note 2)	I_{DM}	1.5	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_{DTOT}	2.5	W
Single Pulsed Avalanche Energy ^(Note 3)	E_{AS}	62	mJ
Single Pulsed Avalanche Current ^(Note 3)	I_{AS}	2.5	A
Operating Junction Temperature	T_J	150	°C
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	°C

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	15	°C/W
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	55.8	°C/W

Notes: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	600	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2	--	4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I_{DSS}	--	--	1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 0.6A$	$R_{DS(ON)}$	--	3.6	5	Ω
Forward Transconductance	$V_{DS} = 10V, I_D = 0.2A$	g_{fs}	--	0.8	--	S
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 400V, I_D = 0.6A,$ $V_{GS} = 10V$	Q_g	--	13	--	nC
Gate-Source Charge		Q_{gs}	--	2	--	
Gate-Drain Charge		Q_{gd}	--	6	--	
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $f = 1.0\text{MHz}$	C_{iss}	--	435	--	pF
Output Capacitance		C_{oss}	--	56	--	
Reverse Transfer Capacitance		C_{rss}	--	9.2	--	
Switching (Note 6)						
Turn-On Delay Time	$V_{GS} = 10V, I_D = 0.6A,$ $V_{DD} = 300V, R_G = 18\Omega,$	$t_{d(on)}$	--	12	--	ns
Turn-On Rise Time		t_r	--	21	--	
Turn-Off Delay Time		$t_{d(off)}$	--	30	--	
Turn-Off Fall Time		t_f	--	24	--	
Source-Drain Diode (Note 4)						
Forward On Voltage	$I_S = 0.6A, V_{GS} = 0V$	V_{SD}	--	0.85	1.15	V

Notes:

1. Current limited by package
2. Pulse width limited by the maximum junction temperature
3. $L = 20\text{mH}, I_{AS} = 2.5A, V_{DD} = 50V, R_G = 25\Omega,$ Starting $T_J = 25^\circ\text{C}$
4. Pulse test: $PW \leq 300\mu s,$ duty cycle $\leq 2\%$
5. For DESIGN AID ONLY, not subject to production testing.
6. Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM2N60SCW RPG	SOT-223	2,500pcs / 13" Reel

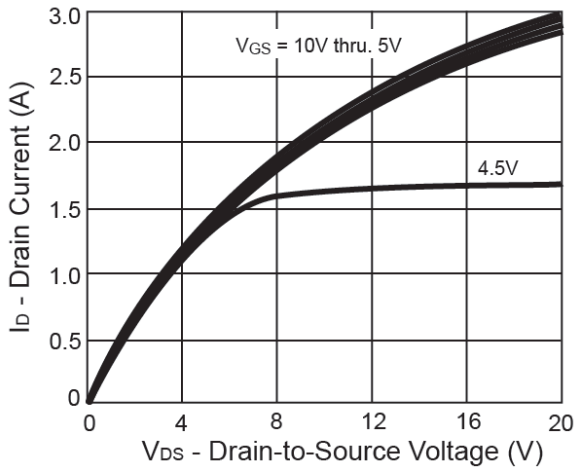
Note:

1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
2. Halogen-free according to IEC 61249-2-21 definition

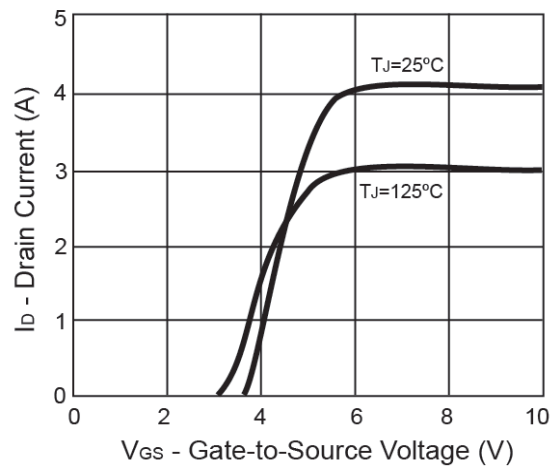
CHARACTERISTICS CURVES

($T_C = 25^\circ\text{C}$ unless otherwise noted)

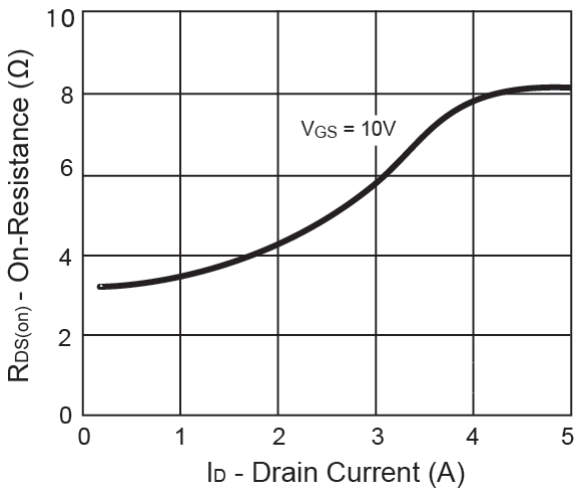
Output Characteristics



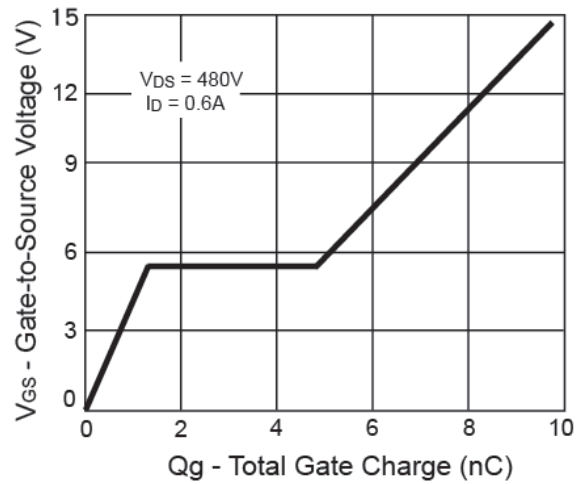
Transfer Characteristics



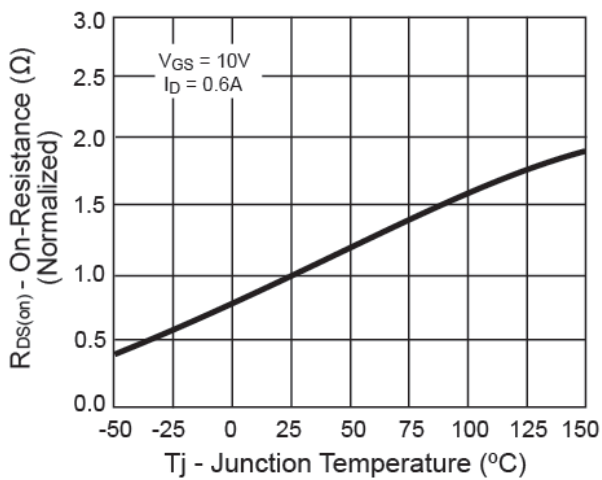
On-Resistance vs. Drain Current



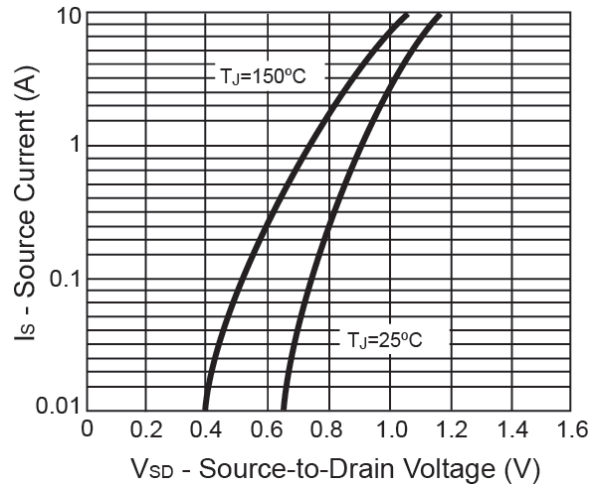
Gate Charge



On-Resistance vs. Junction Temperature



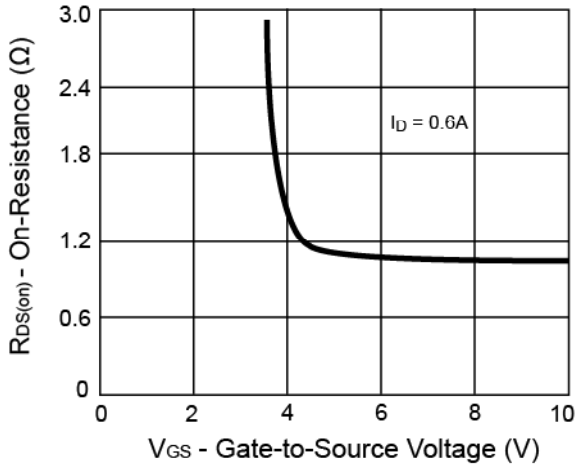
Source-Drain Diode Forward Voltage



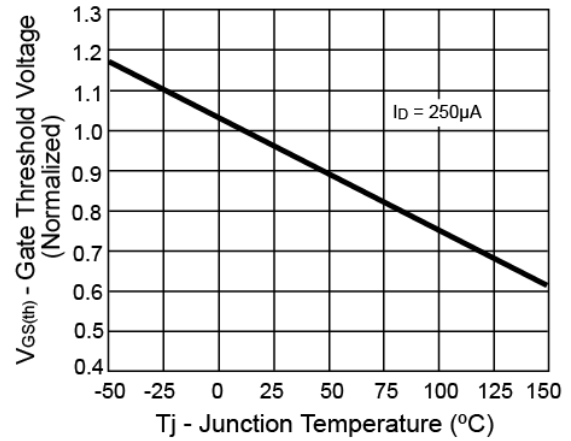
CHARACTERISTICS CURVES

(Tc = 25°C unless otherwise noted)

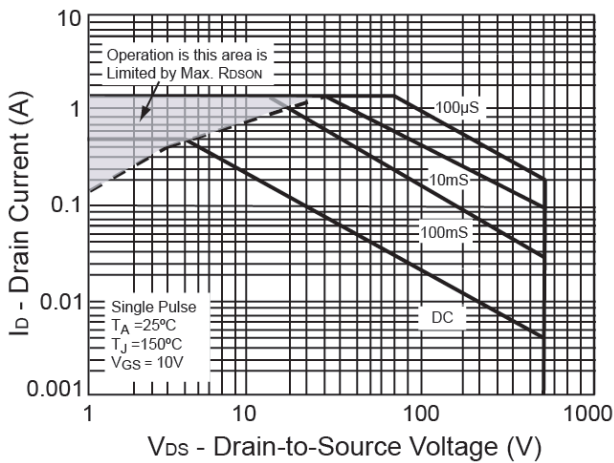
On-Resistance vs. Gate-Source Voltage



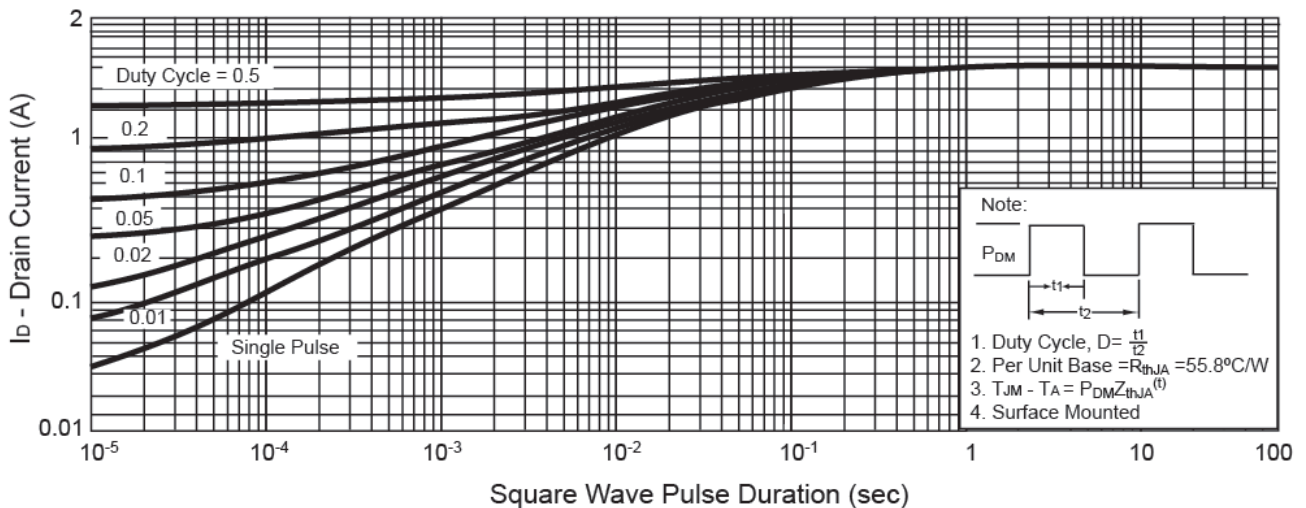
Threshold Voltage



Maximum Safe Operating Area

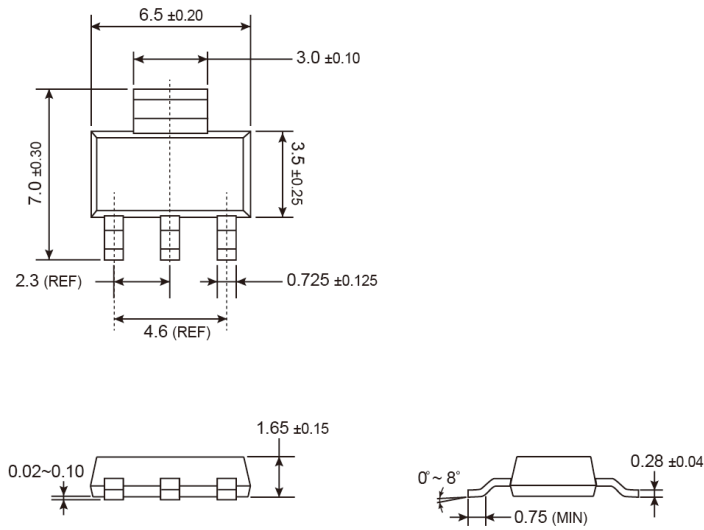


Normalized Thermal Transient Impedance, Junction-to-Ambient

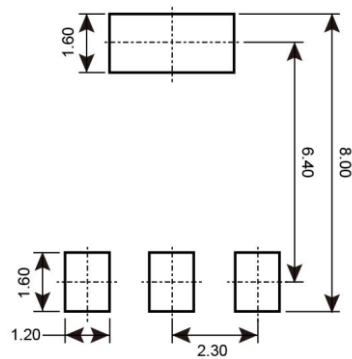


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

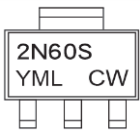
SOT-223



SUGGESTED PAD LAYOUT



MARKING DIAGRAM



- Y** = Year Code
- M** = Month Code for Halogen Free Product
 - O** =Jan **P** =Feb **Q** =Mar **R** =Apr
 - S** =May **T** =Jun **U** =Jul **V** =Aug
 - W** =Sep **X** =Oct **Y** =Nov **Z** =Dec
- L** = Lot Code (1~9, A~Z)

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